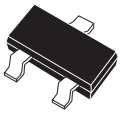
查询CMPT5179供应商

CMPT5179

NPN SILICON RF TRANSISTOR



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5179 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise, high frequency amplifier and high output oscillator applications.

Marking code is C7H.

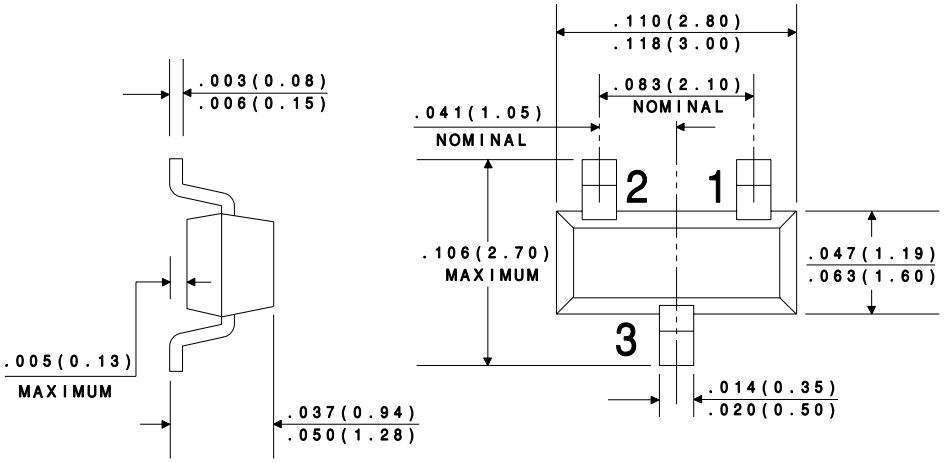
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	2.5	V
Collector Current	I_C	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	V_{CB}=15V			20	nA
BV_{CBO}	I_C=10μA	20			V
BV_{CEO}	I_C=3.0mA	12			V
BV_{EBO}	I_E=10μA	2.5			V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA			0.4	V
$V_{BE(SAT)}$	I_C=10mA, I_B=1.0mA			1.0	V
h_{FE}	V_{CE}=1.0V, I_C=3.0mA	25			
f_T	V_{CE}=6.0V, I_C=5.0mA, f=100MHz	900	1450		MHz
C_{cb}	V_{CB}=10V, I_E=0, f=0.1 to 1.0MHz			1.0	pF
h_{fe}	V_{CE}=6.0V, I_C=2.0, f=1.0kHz	25			
G_{pe}	V_{CE}=6.0V, I_C=5.0mA, f=200MHz	15			dB
NF	V_{CE}=6.0V, I_C=1.5mA, R_S=50Ω, f=200MHz			4.5	dB

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR

R2